# Supporting Information

Systematic Control of Hole-Injection Barrier-Height with Electron Acceptors in [7]phenacene Single Crystal Field-Effect Transistors

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**Table S1. Density of insertion materials used in this study in units of g cm$^{-3}$.**

| Insertion Material | Density | Reference |
|---|---|---|
| $Q(OH)_2$ | 1.65 | D. Semmingsen, Acta Chem. Scand. **B31**, 11 (1977). |
| $QCl_2(OH)_2$ | 1.96 | N. Biliskov *et al.*, J. Phys. Chem. A115, 3154 (2011). |
| $QBr_2(OH)_2$ | 2.53 | C. Robl, Z. Krystallogr. **180** 249 (1987). |
| $QI_4$ | 3.86 | H. Kobayashi *et al*. Bull. Chem. Soc. Jpn. **47**, 2333(1974). |
| $QCl_4$ | 2.02 | Y. Kubozono *et al.* J. Phys. Chem. Solids **58**, 1375 (1997). |
| $Et_2TCNQ$ | 1.18 | Database of SciFinder |
| $Me_2TCNQ$ | 1.25 | Database of SciFinder |
| TCNQ | 1.33 | R. E. Long *et al.* Acta Crystallogr. **1**8, 932 (1965). |
| TNAP | 1.34 | Database of SciFinder |
| DTENF | 1.82 | Database of SciFinder |
| FTCNQ | 1.42 | F. M. Wiygul *et al*. Mol. Cryst. Liq. Cryst. **71**, 303 (1981). |
| $F_2TCNQ$ | 1.52 | F. M. Wiygul *et al*. Mol. Cryst. Liq. Cryst. **78**, 279 (1981). |
| $CF_3TCNQ$ | 1.50 | Database of SciFinder |
| $F_4TCNQ$ | 1.65 | T. J. Emge et al. Mol. Cryst. Liq. Cryst. **65**, 161 (1981). |

The complete author list of reference 19.

[19] Komura, N.; Goto, H.; He, X.; Mitamura, H.; Eguchi, R.; Kaji, Y.; Okamoto, H.; Sugawara, Y.; Gohda, S.; Sato, K. ; Kubozono Y. Characteristics of [6]phenacene Thin Film Field-Effect Transistor. *Appl. Phys. Lett.* **2012**, 101, 083301-1 – 083301-3.